

isc N-Channel MOSFET Transistor

TK16E60W, ITK16E60W

• FEATURES

- Low drain-source on-resistance:
 $R_{DS(on)} \leq 0.19\Omega$.
- Enhancement mode:
 $V_{th} = 2.7$ to $3.7V$ ($V_{DS} = 10V$, $I_D = 0.79mA$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

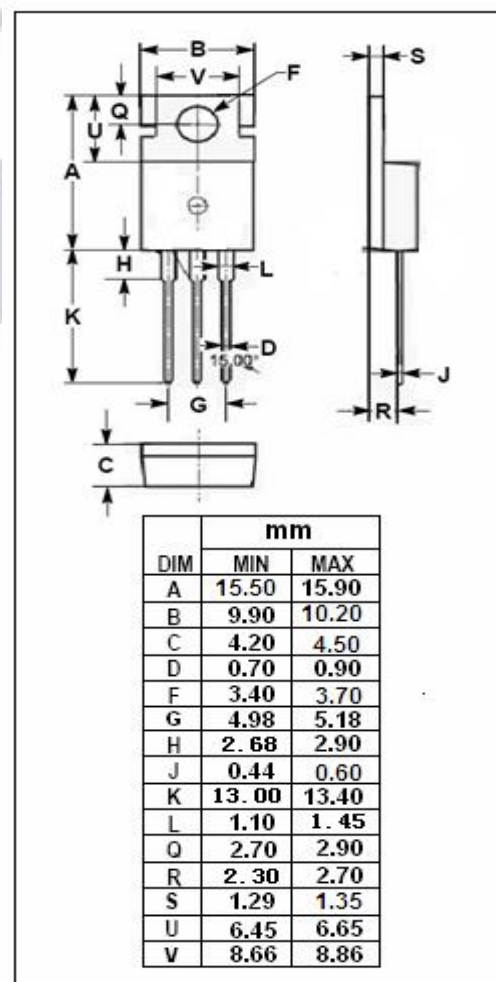
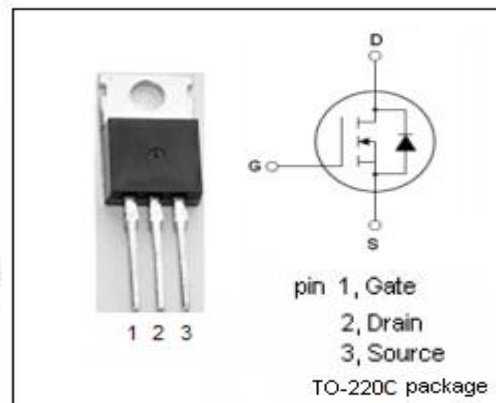
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	15.8	A
I_{DM}	Drain Current-Single Pulsed	63.2	A
P_D	Total Dissipation @ $T_c = 25^\circ C$	130	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.962	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	83.3	$^\circ C/W$



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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=10mA$	600			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10V; I_D=0.79mA$	2.7		3.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=7.9A$			0.19	Ω
I_{GSS}	Gate-Source Leakage Current	$V_{GS}= \pm 30V; V_{DS}= 0V$			± 1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=600V; V_{GS}= 0V$			10	μA
V_{SDF}	Diode forward voltage	$I_{DR} =15.8A, V_{GS} = 0 V$			1.7	V